



VOIDLESS HERMETICALLY SEALED ULTRAFAST RECOVERY GLASS RECTIFIERS

Qualified per MIL-PRF-19500/477

Qualified Levels:
JAN, JANTX,
JANTXV and JANS

DESCRIPTION

This "Ultrafast Recovery" rectifier diode series is military qualified and is ideal for high-reliability applications where a failure cannot be tolerated. The industry-recognized 2.5 amp rated rectifiers with working peak reverse voltages from 50 to 150 volts are hermetically sealed with voidless glass construction using an internal "Category 1" metallurgical bond. These devices are available in both leaded and surface mount MELF package configurations. Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time requirements including standard, fast and ultrafast device types in both through-hole and surface mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 1N5802, 1N5804, 1N5806 series.
- Voidless hermetically sealed glass package.
- Quadruple-layer passivation.
- Extremely robust construction.
- Internal "Category 1" metallurgical bonds.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/477.
- RoHS compliant versions available (commercial grade only).

APPLICATIONS / BENEFITS

- Ultrafast recovery 2.5 amp rectifier series from 50 to 150 V.
- Military, space and other high-reliability applications.
- Switching power supplies or other applications requiring extremely fast switching & low forward loss.
- High forward surge current capability.
- Low thermal resistance.
- Controlled avalanche with peak reverse power capability.
- Inherently radiation hard as described in Microsemi [MicroNote 050](#).

MAXIMUM RATINGS @ T_A = 25°C unless otherwise specified

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +175	°C
Thermal Resistance Junction-to-Lead (L = .375 in) see Figure 1	R _{θJL}	36	°C/W
Working Peak Reverse Voltage: 1N5802 1N5804 1N5806	V _{RWM}	50 100 150	V
Forward Surge Current ⁽³⁾	I _{FSM}	35	A
Average Rectified Output Current @ T _L = +75 °C at 3/8 inch lead length ⁽¹⁾	I _{O1}	2.5	A
Average Rectified Output-Current @ T _A = +55 °C at 3/8 inch lead length ⁽²⁾	I _{O2}	1.0	A
Capacitance @ V _R = 10 V, f = 1 MHz; V _{sig} = 50 mV (p-p)	C	25	pF
Reverse Recovery Time ⁽⁴⁾	t _{rr}	25	ns
Solder Temperature @ 10 s	T _{SP}	260	°C

- Notes:**
1. I_{O1} is rated at 2.5 A @ T_L = 75 °C at 3/8 inch lead length. Derate at 25 mA/°C for T_L above 75 °C.
 2. I_{O2} is rated at 1.0 A @ T_A = 55 °C for PC boards where thermal resistance from mounting point to ambient is sufficiently controlled (R_{θJX} < 154 °C/W) where T_{J(max)} 175 °C is not exceeded. Derate at 8.33 mA/°C for T_A above 55 °C.
 3. T_A = 25 °C @ I_O = 1.0 A and V_{RWM} for ten 8.3 ms surges at 1 minute intervals.
 4. I_F = 0.5 A, I_{RM} = 0.5 A, I_{R(REC)} = .05 A.



"A" Package

Also available in:

**"A" (D-5A) MELF
Package**

(surface mount)



[1N5802, 04, 06US & URS](#)

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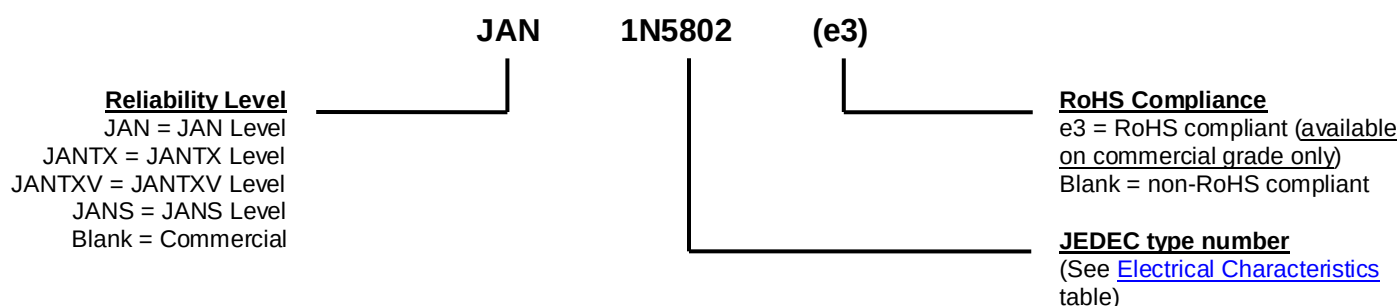
Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hemetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Tin/lead (Sn/Pb) or RoHS compliant matte/tin (commercial grade only) over nickel plate over copper.
- MARKING: Body coated in blue with part number.
- POLARITY: Cathode indicated by band.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 340 milligrams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS

Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
I_O	Average Rectified Output Current: Output current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.
C	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current occurs.

ELECTRICAL CHARACTERISTICS

	BREAKDOWN VOLTAGE (MIN.) @ 100 μ A $V_{(BR)}$	MAXIMUM FORWARD VOLTAGE @ 8.3 ms pulse V_{FM}		REVERSE CURRENT (MAX.) @ V_{RWM} I_R		SURGE CURRENT (MAX) I_{FSM} (Note 1)	REVERSE RECOVERY TIME (MAX) t_{rr} (Note 2)	THERMAL IMPEDANCE @ $t_H = 10$ ms $Z_{\theta JX}$ (Note 3)
TYPE	Volts	Volts		μ A		Amps	ns	$^{\circ}$ C/W
		$I_F = 1.0$ A	$I_F = 2.5$ A	25 $^{\circ}$ C	125 $^{\circ}$ C			
1N5802	60	0.875	0.975	1	175	35	25	4.0
1N5804	110	0.875	0.975	1	175	35	25	4.0
1N5806	160	0.875	0.975	1	175	35	25	4.0

- NOTES:**
1. $T_A = 2.5^{\circ}\text{C}$ @ $I_O = 1.0$ A and V_{RWM} for ten 8.3 ms surges at 1 minute intervals (I_{FSM} surge is also a maximum rating).
 2. $I_F = 0.5$ A, $I_{RM} = 0.5$ A, $I_{R(REC)} = .05$ A (t_{rr} reverse recovery time is also a maximum rating).
 3. For the complete thermal impedance curve over a broad range of heating times, see [Figure 1](#).

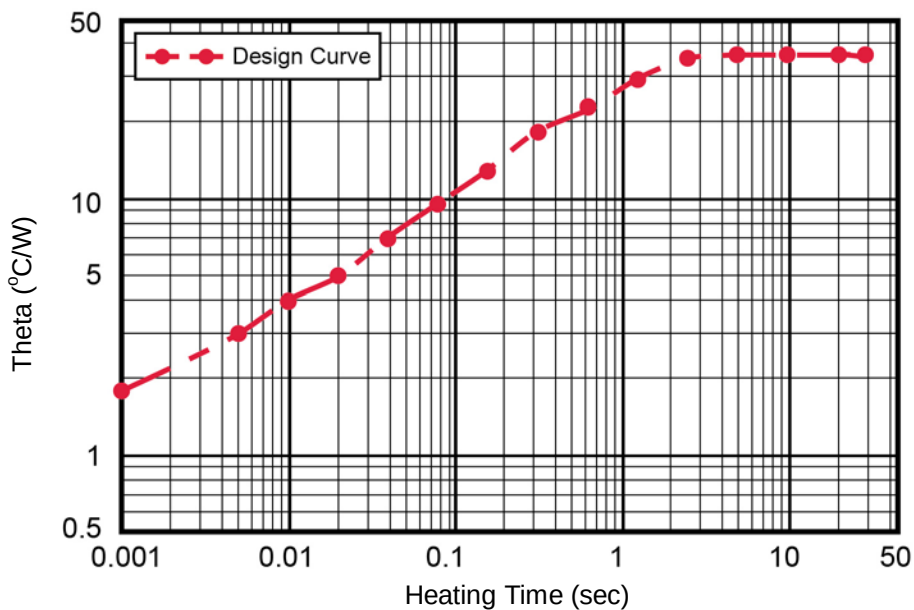
GRAPHS


FIGURE 1
Maximum Thermal Impedance

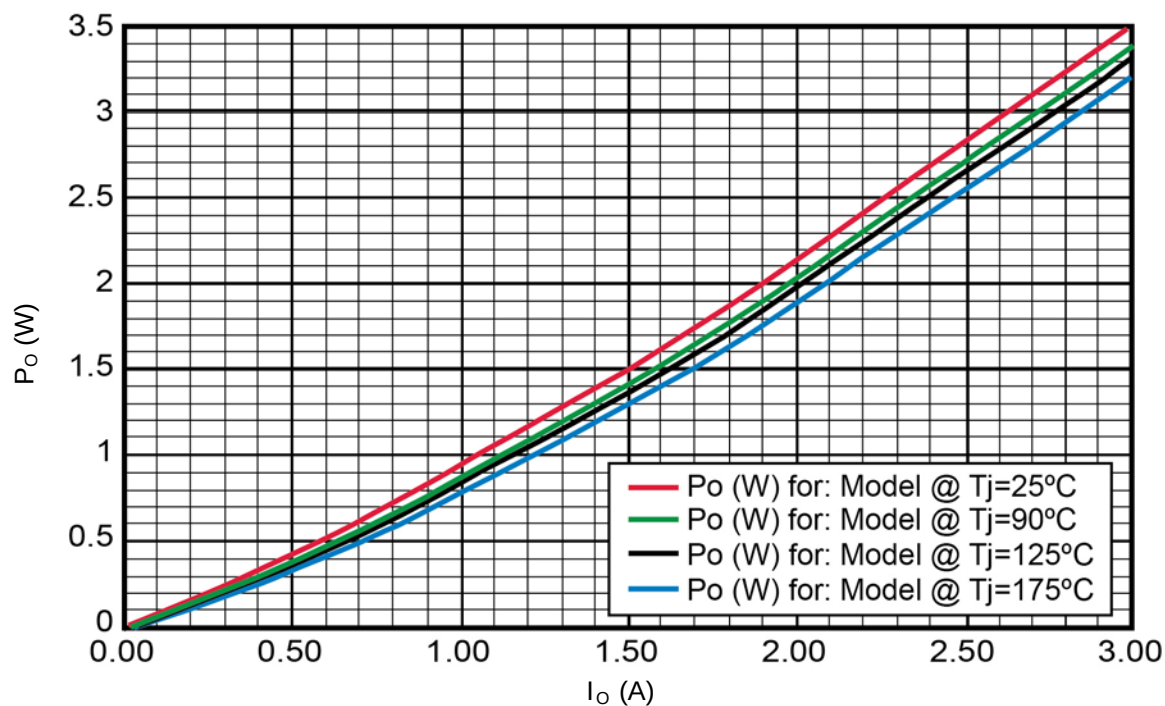
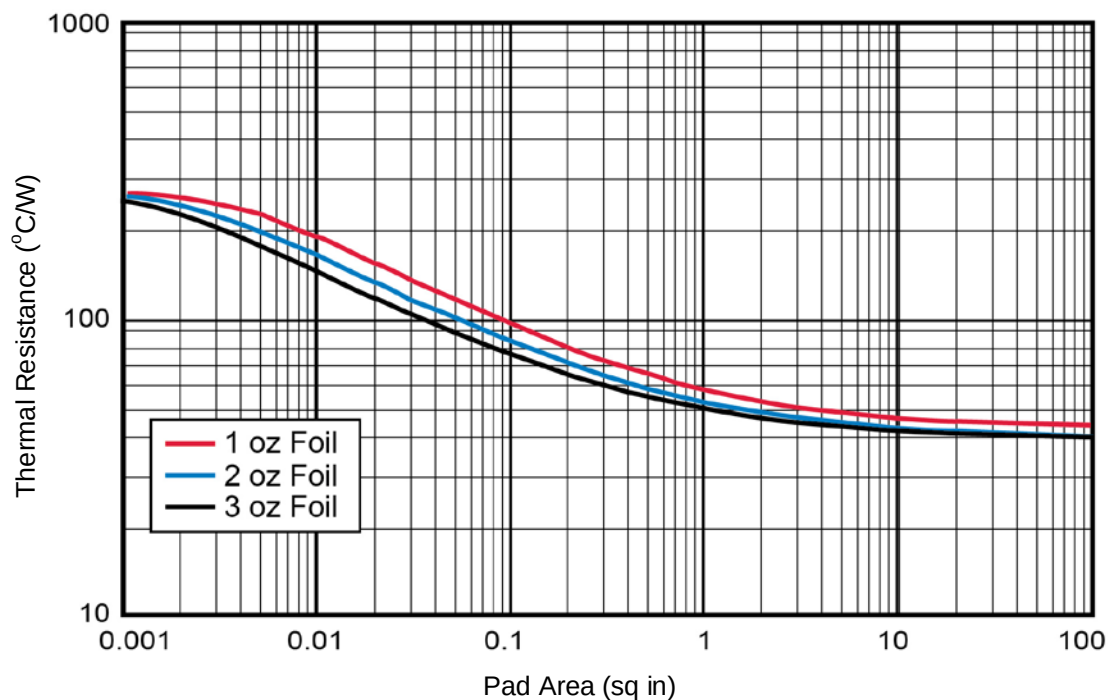
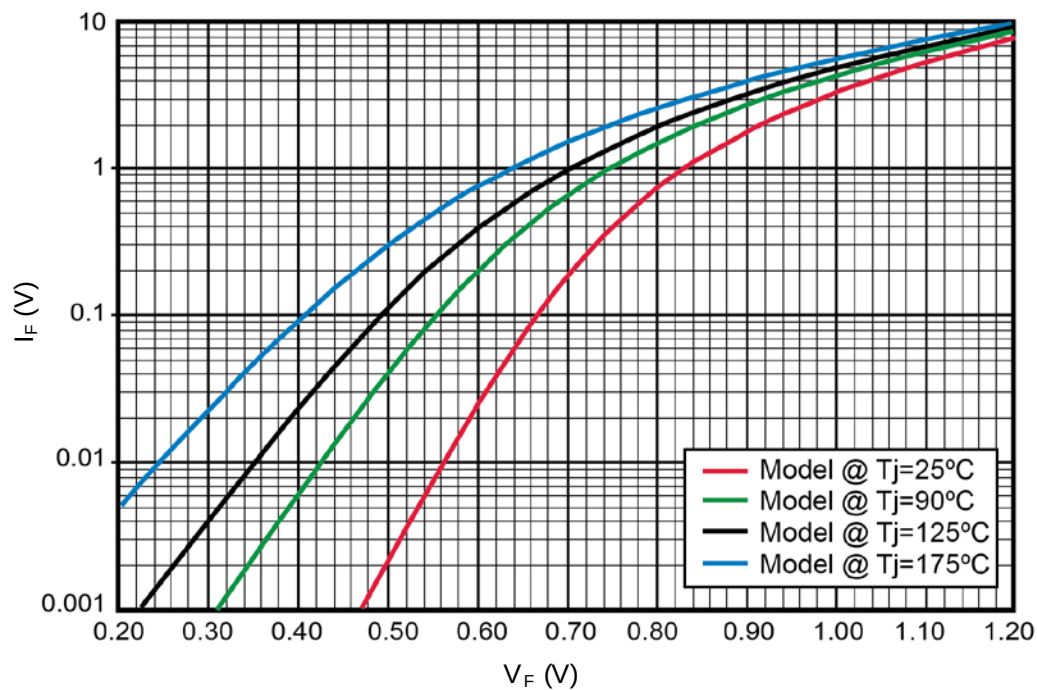


FIGURE 2
Rectifier Power vs I_O (Average Forward Current)

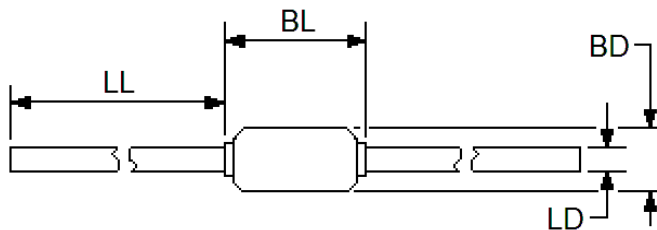
GRAPHS (continued)

FIGURE 3

Thermal Resistance vs FR4 Pad Area At Ambient

PCB horizontal (for each pad) with 1, 2, and 3 oz copper


FIGURE 4

Forward Voltage vs Forward Current

PACKAGE DIMENSIONS

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension BL shall include the entire body including slugs and sections of the lead over which the diameter is uncontrolled. This uncontrolled area is defined as the zone between the edge of the diode body and extending .050 inch (1.27 mm) onto the leads.
4. Dimension BD shall be measured at the largest diameter.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ symbology.

Ltr	DIMENSIONS				Notes
	INCH		MILLIMETERS		
	Min	Max	Min	Max	
BD	.065	.085	1.65	2.16	4
BL	.125	.250	3.18	6.35	3
LD	.027	.032	0.69	0.81	3
LL	.700	1.30	17.78	33.02	

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<http://moschip.ru/get-element>

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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